

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT4122726

SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
CONVEYING PARTY DATA		
Name		Execution Date
MOMENTIVE PERFORMANCE MATERIALS, INC.		07/11/2016
RECEIVING PARTY DATA		
Name:	SORAA INC.	
Street Address:	6500 KAISER DRIVE	
City:	FREMONT	
State/Country:	CALIFORNIA	
Postal Code:	94555	
PROPERTY NUMBERS Total: 41		
Property Type	Number	
Patent Number:	7125453	
Patent Number:	7625446	
Patent Number:	7935382	
Patent Number:	7942970	
Patent Number:	8039412	
Patent Number:	6398867	
Patent Number:	7078731	
Patent Number:	7098487	
Patent Number:	7638815	
Patent Number:	7786503	
Patent Number:	7859008	
Patent Number:	8357945	
Patent Number:	9279193	
Patent Number:	7101433	
Patent Number:	7063741	
Patent Number:	7368015	
Patent Number:	6806508	
Patent Number:	7291544	
Patent Number:	8089097	
Patent Number:	6936488	

PATENT

Property Type	Number
Patent Number:	7053413
Patent Number:	7102158
Patent Number:	7009215
Patent Number:	7582498
Patent Number:	7704324
Patent Number:	7705275
Patent Number:	7642122
Application Number:	60392741
Patent Number:	8216370
Patent Number:	7527742
Patent Number:	6861130
Application Number:	09683658
Application Number:	11376575
Application Number:	11376640
Application Number:	15061069
Application Number:	60435189
Application Number:	60828646
Application Number:	09694690
Application Number:	11249872
Application Number:	61368443
Application Number:	13812757

CORRESPONDENCE DATA

Fax Number: (215)972-7725

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 2159727872

Email: patents@saul.com

Correspondent Name: SAUL EWING LLP

Address Line 1: 1500 MARKET STREET

Address Line 4: PHILADELPHIA, PENNSYLVANIA 19102

ATTORNEY DOCKET NUMBER:	091756-00001
NAME OF SUBMITTER:	STEPHEN J. DRISCOLL
SIGNATURE:	/Stephen J. Driscoll/
DATE SIGNED:	11/01/2016

Total Attachments: 12

source=Soraa Patent Assignment#page1.tif

source=Soraa Patent Assignment#page2.tif

source=Soraa Patent Assignment#page3.tif

source=Soraa Patent Assignment#page4.tif

source=Soraa Patent Assignment#page5.tif
source=Soraa Patent Assignment#page6.tif
source=Soraa Patent Assignment#page7.tif
source=Soraa Patent Assignment#page8.tif
source=Soraa Patent Assignment#page9.tif
source=Soraa Patent Assignment#page10.tif
source=Soraa Patent Assignment#page11.tif
source=Soraa Patent Assignment#page12.tif

EXECUTION COPY

PATENT ASSIGNMENT

This PATENT ASSIGNMENT (this "Assignment") is made as of July 11, 2016 ("Effective Date"), by and between MOMENTIVE PERFORMANCE MATERIALS INC., a Delaware corporation, with a its principal place of business at 260 Hudson River Road, Waterford, NY 12188 ("Seller"); and SORAA INC., a Delaware corporation, with its principal place of business at 6500 Kaiser Drive, Fremont, California 94555 ("Purchaser").

WHEREAS, the parties entered into that certain Patent Transfer Agreement, dated as of May 31, 2016 (as amended through the date hereof, the "Patent Transfer Agreement");

WHEREAS, under the Patent Transfer Agreement, among other things, Seller has agreed to assign its rights in and to the Transferred Patents (as such term is defined in the Patent Transfer Agreement) to Purchaser; and

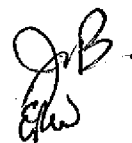
WHEREAS, the parties agree that this Assignment, which is subject to the Patent Transfer Agreement in all respects, accurately describes the Transferred Patents and is intended by the parties to be filed with the relevant governmental authorities to effect registration of the assignment pursuant to the Patent Transfer Agreement of the Transferred Patents;

NOW, THEREFORE, in consideration of the foregoing and the covenants and promises contained herein, the parties agree as follows:

1. Seller does hereby sell, transfer, convey, assign and deliver to Purchaser all of Seller's right, title and interest in the Transferred Patents, including, without limitation, those patents and patent applications listed on Exhibit A to this Assignment in any and all countries, including all divisions, reissues, continuations, and extensions thereof, and all the rights of priority resulting from the filing of said Transferred Patents, and all claims for damages and other remedies for past and future infringements of the Transferred Patents, along with the right to sue for and collect such damages and other remedies for the use and benefit of Purchaser and its successors, assigns and other legal representatives.

2. Seller agrees to execute and deliver any and all affidavits, testimonies, declarations, oaths, samples, exhibits, specimens and other documentation as may be reasonably required to effect the terms of this Assignment and its recordation in relevant state, national or international patent offices.

[signature page follows]



IN WITNESS WHEREOF, the parties have executed this Assignment by their respective authorized representatives as of the Effective Date.

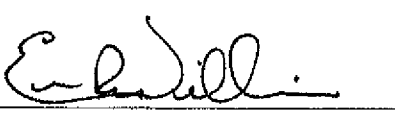
**MOMENTIVE PERFORMANCE
MATERIALS INC.**

By: 

Title: PRESIDENT & CEO

Date: 7/11/2016

SORAA INC.

By: 

Title: CEO

Date: 7/11/2016

EXHIBIT A

TRANSFERRED PATENTS

Serial	Country	Class	Status	Application Number	Publication Number	Patent Number	Grant Date	Term Date	Title
121655-04	JAPAN	PCT	GRANTED	2003-553702	JP200515584 (A)	JP4451662B2	2/5/2010	11/22/2002	Pressure Vessel
121655-09	GERMANY	EPC	GRANTED	DE3002614438	DE60214436 (T2)	DE60214436D1	10/12/2006	11/22/2002	Pressure Vessel
121655-10	FRANCE	EPC	GRANTED	02789868.3	EP 1476249 T2	EP 1476249 B1	8/30/2006	11/22/2002	Improved pressure vessel
121655-03	EPO	PCT	GRANTED	2002.789868	EP1476249 (A1)	EP1476249 (B1)	8/30/2006	11/22/2002	Improved pressure vessel
RD26623-01	USA	ORIG	GRANTED	08/663658	US2003-0141301A1	7125453	10/24/2006	1/31/2002	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-10	USA	DIV	GRANTED	11/010139	US2005-0152820A1	7625446	12/1/2009	12/10/2004	High temperature high pressure capsule for processing materials in supercritical fluids
152419-04	KOREA (SOUTH)	PCT	GRANTED	2003-7015178	KR20060078691	KR101351498B	1/15/2014	12/20/2005	Crystalline composition, device, and associated method
162419-04	JAPAN	PCT	GRANTED	2006-547331	JP2009620678A	JP5143016B2	2/13/2013	12/20/2005	Crystalline composition, device, and associated method
162419-04	EUROPE	PCT	PENDING	06845438.8	EP1977029A2			12/15/2006	Crystalline composition, device, and associated method
162419-04	CHINA	PCT	GRANTED	220680053099.5	CN101379227 (A)	CN101379227 (B)	6/12/2013	12/15/2006	Crystalline composition, device, and associated method
162419-03	USA	ORIG	GRANTED	11/313526	US2007-0141819 A1	7936382	5/3/2011	12/20/2005	METHOD FOR MAKING CRYSTALLINE COMPOSITION
162419-02	USA	ORIG	GRANTED	11/313442	US2007-0151609 A1	7942970	5/17/2011	12/20/2005	APPARATUS FOR MAKING CRYSTALLINE COMPOSITION
162419-01	USA	ORIG	GRANTED	11/313451	US2007-0142204 A1	8089412	10/18/2011	12/20/2005	CRYSTALLINE COMPOSITION, DEVICE, AND ASSOCIATED METHOD
RD27007-07	EUROPE	EPC	GRANTED	EP00867038.9	EP1230005A1	EP1230005B1	1/3/2007	9/29/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-10	KOREA (SOUTH)	PCT	GRANTED	10-2002-7004411	10-2002-0042705	10-07620190000	9/19/2007	9/29/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride

J.B. [Signature]

Patent No.	Country	App. No.	Status	Application Date	Publication Number	Publication Date	Grant Date	Term Date	Title
RD27007-08	JAPAN	PCT	GRANTED	2001-527911	JP4942270B	5/30/2012	9/29/2000		Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-07	GERMANY	EPC	GRANTED	00967039.9	DE6003279372	2/15/2007	9/28/2000		Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-07	FRANCE	EPC	GRANTED	00967039.9	EP1230005A1	1/3/2007	9/28/2000		Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-07	NETHERLANDS	EPC	GRANTED	00967039.9	EP1230005B1	1/3/2007	9/28/2000		Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-04	USA	ORIG	GRANTED	09/413446	Non-pub	6/4/2002	10/6/1999		Crystalline gallium nitride and method for forming crystalline gallium nitride
130575-08	SINGAPORE	PCT	GRANTED	200503618-1	SG112630	7/3/12007	12/22/2003		Gallium nitride crystal and method of making same
130575-06	KOREA (SOUTH)		GRANTED	10-2005-7012173	KR101293352	8/5/2013	6/27/2005		Gallium nitride crystal and method of making same
130575-06A	KOREA (SOUTH)	DIV	GRANTED	10-2012-7015773	KR101294832	7/4/2013	6/19/2012		Gallium nitride crystal and method of making same
130575-11-1	JAPAN	DIV	PENDING	2013-131452	JP2013251552A		6/24/2013		Method Associated with a Crystalline Composition and Wafer
130575-12	JAPAN	PCT	REFUSED	2009-534644	JP2010-507561A		10/25/2007		Gallium nitride crystal and method of making same
130575-05	JAPAN	PCT	GRANTED	2004-566702	JP5159023	3/6/2013	12/22/2003		Gallium nitride crystal and method of making same
130575-06-1	JAPAN	DIV	GRANTED	2012-231691	JP5684769	3/19/2015	10/19/2012		Gallium nitride crystal and method of making same
130575-13	EUROPE	PCT	PENDING	07867412.4	EP2102391		11/9/2007		Nitride Crystals and Wafers
130575-14	EUROPE	PCT	PENDING	08713079.5	EP2122016		1/9/2008		Crystalline composition, wafer, and semiconductor structure
130575-15	EUROPE	PCT	PENDING	08713077.9	EP210895A2		1/9/2008		Crystalline Gallium Nitride and Associated Wafer and Device
130575-04	EUROPE		PENDING	08800171.5	EP1576486 A		12/22/2003		Gallium nitride crystal, homoepitaxial gallium-nitride-based devices and method for producing same
130575-12	CHINA	PCT	ABANDONED	200780039786.5	CN101573479 A		10/25/2007		Nitrogen of gallium crystal body to and methods for their preparation
130575-13-1	CHINA	DIV	PENDING	CN201310078174.5	CN1031457129 A		11/9/2007		Method for growing a crystalline composition comprising gallium nitride
130575-14	CHINA	PCT	ABANDONED	200860007693.X	CN101641453 A		1/9/2008		Crystalline composition, wafer, device, and associated method

J.B. Edwards

Patent No.	Country	Applicant	Status	Pub. No.	Pub. Date	Pub. Title	Grant Date	Term Date	Title	
13057-S-07	CHINA	PCT	GRANTED	200380108711.2		CN1748230 (A)	CN100474511	4/1/2009	12/22/2003	Gallium nitride crystal, homoepitaxial gallium-nitride-based devices and method for producing same
13057-S-03	USA	CIP	GRANTED	11/010507		US2005-0058095 A1	7078731	7/18/2006	12/13/2004	GALLIUM NITRIDE CRYSTALS AND WAFERS AND METHOD OF MAKING
13057-S-01	USA	ORIG	GRANTED	10/328981		US2004-0124434 A1	7098487	8/29/2006	12/27/2002	Gallium nitride crystal and method of making same
13057-S-16	USA	CIP	GRANTED	11/621560		US2006-0008855 A1	7638815	12/29/2009	1/9/2007	CRYSTALLINE COMPOSITION, WAFER, AND SEMI-CONDUCTOR STRUCTURE
13057-S-13	USA	CIP	GRANTED	11/559146		US2007-0158785 A1	7786503	8/31/2010	11/13/2006	GALLIUM NITRIDE CRYSTALS AND WAFERS AND METHOD OF MAKING
13057-S-14	USA	CIP	GRANTED	11/621556		US2006-0006944 A1	7659008	12/29/2010	1/9/2007	CRYSTALLINE COMPOSITION, WAFER, DEVICE, AND ASSOCIATED METHOD
13057-S-12	USA	CIP	GRANTED	11/588181		US2007-0215897 A1	8357945	1/22/2013	10/29/2006	GALLIUM NITRIDE CRYSTAL AND METHOD OF MAKING SAME
13057-S-11	USA	CIP	GRANTED	11/558048		US2012-0017825 A1	9279193	3/8/2016	11/9/2006	Method of making a gallium nitride crystalline composition having a low dislocation density
130684-02	USA	Non Prov	GRANTED	10/699504		US2004-0194415 A1	7101433	9/5/2006	10/31/2003	HIGH PRESSURE/HIGH TEMPERATURE APPARATUS WITH IMPROVED TEMPERATURE CONTROL FOR CRYSTAL GROWTH
RD29614-01	USA	ORIG	GRANTED	10/063164		US2003-0183165 A1	7063741	6/20/2006	3/27/2002	HIGH PRESSURE HIGH TEMPERATURE GROWTH OF CRYSTALLINE GROUP III METAL NITRIDES
RD29614-03	UNITED KINGDOM	EPC	GRANTED	06709199.8		EP1490537 (A1)	EP1490537	4/13/2011	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-09	SOUTH AFRICA	PCT	GRANTED	21-01-2004/8200		ZA2004/08200 (A)	ZA2004/8200	11/30/2005	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-07	KOREA (SOUTH)	PCT	GRANTED	20047015545		KR2004/0097248 (A)	KR100987850	10/13/2010	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-03	GERMANY	EPC	GRANTED	03709189.8			EP1490537	4/13/2011	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-03	FRANCE	EPC	GRANTED	03709189.8			EP1490537	4/13/2011	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-03	EUROPE	PCT	GRANTED	03709189.8		EP1490537A1	EP1490537	4/13/2011	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-05	CHINA	PCT	GRANTED	03806903.7		CN1643187 (A)	CN100354458	12/12/2007	2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-11	USA	CIP	GRANTED	11/243896		US2006-0048699 A1	7368015	5/6/2008	10/13/2005	APPARATUS FOR PRODUCING SINGLE CRYSTAL AND QUASI-SINGLE CRYSTAL AND ASSOCIATED METHOD

Serial	Country	App No.	Status	Pub. No.	Pub. Date	Pat. No.	Pat. Date	Pub. Date	Title
RD27966-02	USA	ORIG	GRANTED	09/639941	US2002-0156634 A1	6606508	10/19/2004	4/20/2001	HOMOEPITAXIAL GALLIUM NITRIDE BASED PHOTODETECTOR AND METHOD OF PRODUCING
RD27966-03	USA	DIV	GRANTED	10/932127	US2005-0028637 A1	7291544	11/6/2007	9/1/2004	HOMOEPITAXIAL GALLIUM NITRIDE BASED PHOTODETECTOR AND METHOD OF PRODUCING
RD29634-01	USA	ORIG	GRANTED	10/329982	US2004-0124455 A1	8089087	1/3/2012	12/27/2002	HOMOEPITAXIAL GALLIUM NITRIDE BASED ELECTRONIC DEVICES AND METHOD FOR PRODUCING SAME
RD27904-03	USA	DIV	GRANTED	10/440574	US2004-0031978 A1	6966488	8/30/2005	5/19/2003	Homoepitaxial gallium-nitride-based light emitting device and method for producing
RD27904-04	USA	CIP	GRANTED	10/531865	US2004-0245535 A1	7053413	5/30/2005	4/26/2004	Homoepitaxial gallium-nitride-based light emitting device and method for producing
RD27904-05	USA	CIP	GRANTED	10/746292	US2004-0196598 A1	7102158	8/5/2006	12/29/2003	Light-based system for detecting analytes
132852-01	USA	ORIG	GRANTED	10/693803	US2005-0087753 A1	7009215	3/7/2006	10/24/2003	Group III-nitride based resonant cavity light emitting devices fabricated on single crystal gallium nitride substrates
132852-07	USA	CIP	GRANTED	11/295627	US2006-0118799 A1	7562498	8/1/2009	12/6/2005	Resonant cavity light emitting devices and associated method
132852-03	NETHERLANDS	EPC	GRANTED	04796085.1		EP1680817	8/1/2012	10/22/2004	Group III-Nitride Based Resonant Cavity Light Emitting Devices Fabricated on Single Crystal Gallium Nitride Substrates and Method for Their Production
132852-06	KOREA (SOUTH)	PCT	GRANTED	2005-7020687	KR20060097558 (A)	KR101283307	7/30/2013	10/22/2004	Group III-nitride based resonant cavity light emitting devices fabricated on single crystal gallium nitride substrates
132852-04	JAPAN	PCT	PENDING	2006-539820	JP2007509607			10/22/2004	Group III-nitride Based Resonant Cavity Light Emitting Devices Fabricated on Single Crystal Gallium Nitride Substrates and Method for Their Production
132852-03	GERMANY	EPC	GRANTED	04796085.1		EP1680817	8/1/2012	10/22/2004	Group III-Nitride Based Resonant Cavity Light Emitting Devices Fabricated on Single Crystal Gallium Nitride Substrates and Method for Their Production
132852-05	FRANCE	EPC	GRANTED	04796085.1		EP1680817	8/1/2012	10/22/2004	Group III-Nitride Based Resonant Cavity Light Emitting Devices Fabricated on Single Crystal Gallium Nitride Substrates and Method for Their Production
132852-08	EUROPE	PCT	GRANTED	04796085.1	EP20040796085	EP1680817	8/1/2012	10/22/2004	Group III-Nitride Based Resonant Cavity Light Emitting Devices Fabricated on Single Crystal Gallium Nitride Substrates and Method for Their Production
132852-05	CHINA	PCT	GRANTED	200480015116.7	CN1799150A	CN100472821C	3/25/2009	10/22/2004	Group III-nitride based resonant cavity light emitting devices fabricated on single crystal gallium nitride substrates
155898-01	USA	ORIG	GRANTED	11/042858	US2006-0177362 A1	7704324	4/27/2010	1/25/2005	APPARATUS FOR PROCESSING MATERIALS IN SUPERCRITICAL FLUIDS AND METHODS THEREOF

[Handwritten signature]

Serial Number	Country	Patent Type	Status	Application Number	Publication Number	Patent Number	Grant Date	Term Date	Title
155899-03	RUSSIAN FEDERAT	PCT	GRANTED	2007132167	RU2007132167 (A)	RU2393008 (C2)	6/27/2010	10/19/2005	Apparatus and Methods for Treatment of Materials in Supercritical Fluid Media
155899-03-1	POLAND	EDV	PENDING	10011809.0	EP2295135 (A1)			10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03	POLAND	EPC	GRANTED	EP06511853.0	EP1846148 (A1)	EP1846148 B1	12/22/2010	10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03-1	NETHERLANDS	EDV	PENDING	10011809.0	EP2295135 (A1)				Apparatus for processing materials in supercritical fluids
155899-03	NETHERLANDS	EPC	GRANTED	06511853.0	EP1846148 (A1)	EP1846148	12/22/2010	10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03-1	GERMANY	EDV	PENDING	10011809.0	EP2295135 (A1)				Apparatus for processing materials in supercritical fluids
155899-03	GERMANY	EPC	GRANTED	06511853.0	EP1846148 (A1)	EP1846148	12/22/2010	10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03-1	FRANCE	EDV	PENDING	10011809.0	EP2295135 (A1)				Apparatus for processing materials in supercritical fluids
155899-03	FRANCE	EPC	GRANTED	06511853.0	EP1846148 (A1)	EP1846148 B1	12/22/2010	10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03-1	EUROPE	DIV	PENDING	EP20100011809	EP2295135 (A1)			10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03	EUROPE	PCT	GRANTED	EP20050811853	EP1846148 (A1)	EP1846148 B1	12/22/2010	10/19/2005	Apparatus for processing materials in supercritical fluids
155899-03	CHINA	PCT	GRANTED	200560047233.6	CN101163540A	CN101163540B	4/13/2011	10/19/2005	Apparatus for processing materials in supercritical fluids and methods thereof
167206-02	USA	ORIG	GRANTED	11/621064	US2006-0063741 A1	7765275	4/27/2010	9/14/2006	Heater, Apparatus, and Associated Method
167206-05	KOREA (SOUTH)		GRANTED	20060120252	KR20060024939	KR101310437	9/25/2013	11/30/2006	Heater, Apparatus, and Associated Method
167206-05	JAPAN		GRANTED	2006-323731	JP2008071728	JP5044202	10/10/2012	11/30/2006	Heater, Apparatus, and Associated Method
167206-04	EUROPE		GRANTED	EP06024819.2	EP1901584	EP1901584	03/30/2016	11/30/2006	Heater, Apparatus, and Associated Method
167206-04	FRANCE	EPC	GRANTED	EP06024819.2	EP1901584	EP1901584	03/30/2016	11/30/2006	Heater, Apparatus, and Associated Method
167206-04	POLAND	EPC	GRANTED	EP06024819.2	EP1901584	EP1901584	03/30/2016	11/30/2006	Heater, Apparatus, and Associated Method
167206-03	CHINA		GRANTED	200610084789.2	CN101146579	CN101146579	11/19/2011	11/30/2006	Heater, Apparatus, and Associated Method

Serial Number	Country	Case No.	Status	Publication Date	Publication Number	Examination Number	Examination Date	Filing Date	Title
133035-02	USA	Non-Prov	GRANTED	11/9/2012	US2008-0087919 A1	7642122	1/5/2010	10/5/2007	Method for forming nitride crystals
133035-03	JAPAN	PCT	GRANTED	2009-03-14-09	JP2010050730A	JP5480624B2	4/23/2014	10/5/2007	Method for forming nitride crystals
133035-03	EUROPE	PCT	PENDING	07852559.9	EP2078105			10/5/2007	Method for forming nitride crystals
133035-03	CHINA	PCT	ABANDONED	200700037599.4	CN101535532			10/5/2007	Method for forming nitride crystals
133035-03-1	CHINA	DNV	ABANDONED	201310081062.5	CN103184519			10/5/2007	Method for forming nitride crystals
126452	USA	Prov	EXPIRED	60/392741				6/27/2002	Method for reducing defect concentrations in crystals
126452-06	USA	DNV	GRANTED	11/300650	US2006-0096521 A1	6216370	7/10/2012	12/12/2005	Method for reducing defect concentrations in crystals
145822-01	USA	ORIG	GRANTED	11/167719	US2006-0289386 A1	7527742	5/5/2009	6/27/2005	ETCHANT, METHOD OF ETCHING, LAMINATE FORMED THEREBY, AND DEVICE
145822-03	KOREA (SOUTH)		GRANTED	10-2006-0115389	KR20070000328 (A)	KR101242309 (B1)	3/1/2013	11/30/2005	ETCHANT, METHOD OF ETCHING, LAMINATE FORMED THEREBY, AND DEVICE
145822-02	JAPAN		GRANTED	JP2005-337964	JP2007005752 (A)	JP4895631	3/14/2012	11/24/2005	ETCHING AGENT, ETCHING METHOD, AND FORMED LAMINATE AND DEVICE
120451-01	USA	ORIG	GRANTED	10/001575	US2003-0086856 A1	6981130	3/1/2005	11/2/2001	Sintered polycrystalline gallium nitride and its production
120451-06	KOREA (SOUTH)	PCT	GRANTED	10-2004-7006467	1020040053234	10-0903251	6/9/2009	4/29/2004	Sintered polycrystalline gallium nitride
120451-04	JAPAN		GRANTED	2003-543080	2005-508622A	4349807B2	10/27/2009	10/30/2002	Sintered polycrystalline gallium nitride
120451-05	CHINA	PCT	GRANTED	02821830.2	CN1582255A	CN1250182C	10/18/2006	10/30/2002	Sintered polycrystalline gallium nitride
120451-02	WIPO	CON	CLOSED	PCT/US2002034792	WO2003/041138			10/30/2002	Sintered polycrystalline gallium nitride
120451-03	EUROPE	PCT	REFUSED	2002798172				4/28/2004	Sintered polycrystalline gallium nitride
120451-07	SOUTH AFRICA	PCT	LAPSED	2004/03763		2004/03783	1/25/2006	5/17/2004	Sintered polycrystalline gallium nitride
120451-08	POLAND	PCT	ABANDONED	2002-368506	PL368505A1			10/30/2002	Sintered polycrystalline gallium nitride
120451-14	AUSTRALIA	PCT	LAPSED	2002-363469	WO2003/041138			10/30/2002	Sintered polycrystalline gallium nitride

Pub. No.	Country	App. No.	Status	App. No.	Pub. No.	Pub. Date	Filing Date	Pub.
121655-01	USA		ABANDONED	08/633658	US2003-0140845 A1		1/31/2002	Pressure vessel
121655-02	WIPO	PCT	CLOSED	PCT/US02/37755	WO2003064021		11/22/2002	Improved Pressure vessel
121655-05	KOREA (SOUTH)	PCT	ABANDONED	10-2004-701747	KR20040078682 (A)		11/22/2002	Improved pressure vessel
121655-06	CHINA	PCT	ABANDONED	02828503.4	CN1744942 (A)	CN100858621 (C)	1/22/2008	Improved pressure vessel
121655-07	SOUTH AFRICA	PCT	ABANDONED	21-01-2004/06505		2004/06505	11/30/2005	Improved pressure vessel
121655-08	POLAND	EPC	ABANDONED	P.371733	PL371733 (A1)		11/22/2002	Improved pressure vessel
121655-12	SWEDEN	EPC	ABANDONED		SE1476249 T3		8/30/2006	Improved pressure vessel
121655-A	AUSTRIA	EPC	LAPSED		AT337850		8/30/2006	Improved pressure vessel
121655-B	AUSTRALIA	PCT	ABANDONED	2002352908	AU2002352908		10/1/2004	Improved pressure vessel
130575-02	WIPO	PCT	CLOSED	PCT/US03/41255	WO2004061923		12/22/2003	Gallium nitride crystal, homoepitaxial gallium-nitride-based devices and method for producing same
130575-09	USA	CIP	ABANDONED	11/376575	US2007-0040181 A1		3/15/2006	Crystalline composition, water, and semi-conductor structure
130575-10	USA	CIP	ABANDONED	11/376640	US2006-0169986 A1		3/15/2006	Crystalline composition, water, and semi-conductor structure
130575-11	WIPO	PCT	CLOSED	PCT/US07/23693	WO2008133653		11/9/2007	Method for growing a crystalline composition comprising gallium nitride
130575-11	EUROPE	PCT	ABANDONED	7674125.3	EP20999956		11/9/2007	Method for growing a crystalline composition comprising gallium nitride
130575-11	JAPAN	PCT	REFUSED	2005638327	JP2010508172		11/9/2007	Method for growing a crystalline composition comprising gallium nitride
130575-13	CHINA	PCT	ABANDONED	CN200730048549.8	CN101555245 A		11/9/2007	Method for growing a crystalline composition comprising gallium nitride
130575-13-2	CHINA	DIV	PENDING	CN201510259501.6	CN104894645 A		11/9/2007	Method associated with a crystalline composition and water
130575-12	WIPO	PCT	CLOSED	PCT/US07/22582	WO2008051585		10/25/2007	Gallium nitride crystal and method of making same
130575-12	EUROPE	PCT	ABANDONED	EP20070867277	EP2132365A2		10/25/2007	Gallium nitride crystal

Serial	Country	Status	Applicant Name	Patent Number	Grant Date	Issue Date	File
130575-12	TAIWAN	CON	ABANDONED	96138508	TW200333962		Gallium nitride crystal and method of making same
130575-13	WIPO	PCT	CLOSED	PCT/US07/23694	WO2008068444		Gallium nitride crystal and method of making same
130575-11	CHINA	PCT	ABANDONED	200780048761.4	CN101563744 A		Gallium nitride crystals and wafers and method of making
130575-13	JAPAN	PCT	REFUSED	2008537166	JP2010509178A		Gallium nitride crystals and wafers
130575-14	WIPO	PCT	CLOSED	PCT/US08/00302	WO2008085998		Crystalline composition, wafer, device, and associated method
130575-14	JAPAN	PCT	REFUSED	JP2008645587	JP2010515654A		Crystalline compositions, wafers, devices and related methods
130575-15	WIPO	PCT	CLOSED	PCT/US08/00304	WO2008086000		Crystalline composition, wafer, device, and associated method
130575-15	CHINA	PCT	ABANDONED	CN20086007861	CN101691902A		Gallium nitride crystal and method of making same
130575-11-1	USA	CON	PENDING	15/061069			Method of making a gallium nitride crystalline composition having a low dislocation density
130894-01	USA	PROV	EXPIRED	60435189			High pressure/high temperature apparatus with improved temperature control for crystal growth
130894-03	WIPO	PCT	CLOSED	PCT/US08/38687	WO2004060548		High pressure/high temperature apparatus with improved temperature control for crystal growth
130894-04	EUROPE	PCT	ABANDONED	EP03796665	EP1575687		High pressure apparatus for crystal growth
130894-05	JAPAN	PCT	REFUSED	2004565218	JP2006511341		High-pressure, high-temperature device temperature control has been improved for the crystal growth
130894-06	CHINA	PCT	ABANDONED	CN200380109114	CN1777472		High-pressure device for crystal growth
130894-07	KOREA	PCT	ABANDONED	KR20057011140	KR20050265713		High pressure/high temperature apparatus with improved temperature control for crystal growth
130894-08	SOUTH AFRICA	PCT	ABANDONED	200505405	ZA200505405		High pressure apparatus for crystal growth
130894-09	POLAND	PCT	ABANDONED	37592403	PL375924		High pressure/high temperature apparatus with improved temperature control for crystal growth
130894	AUSTRALIA	PCT	ABANDONED	2003298623	AU2003298623		High pressure apparatus for crystal growth

J. B. Jones

Serial	Country	Class	Status	Application Number	Publication Number	Patent Number	Grant Date	Filing Date	Title
132852-02	WIPO	PCT	CLOSED	PCT/US04/35028	WO2005043638			10/22/2004	Group II-nitride based resonant cavity light emitting devices fabricated on single crystal gallium nitride substrates
133035-01	USA	PROV	EXPIRED	60/828646				10/8/2006	Method for Forming Nitride Crystals
133035-03	WIPO	PCT	CLOSED	PCT/US07/21420	WO2008045337			10/5/2007	Method for Forming Nitride Crystals
155899-03	WIPO	PCT	CLOSED	PCT/US05/37434	WO2006080859			10/19/2005	Improved apparatus for high temperature high pressure processing
155899-03	SOUTH AFRICA		LAPSED	21-01-2007/06103	ZA200706103 (A)		2/25/2009	7/24/2007	Improved apparatus for high temperature high pressure processing
155899-03	TAIWAN		ABANDONED	94141741	TW2006050508 (A)			11/28/2005	Apparatus for processing materials in supercritical fluids and methods thereof
162419-04	WIPO	PCT	CLOSED	PCT/US06/47743	WO2007-078844			12/15/2006	Crystalline composition, device, and associated method
162419-04	RUSSIA	PCT	ABANDONED	RU20080129659	RU2008129659			12/15/2006	Crystalline composition, device, and associated method
RD26623-02	WIPO	PCT	CLOSED	PCT/US2003/004253	WO2004-071649			2/12/2003	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-03	EUROPE	PCT	ABANDONED	03711005.3	EP1694503A1			2/12/2003	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-04	JAPAN	PCT	REJECTED	JP2004-568274	JP2006-514581A			2/12/2003	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-05	INDIA	PCT	GRANTED	851/DELNP/2005		IN233070	3/27/2009	3/4/2005	High temperature high pressure capsule
RD26623-06	CHINA	PCT	ABANDONED	03817165.1	CN1668370	CN100376317C	3/25/2008	2/12/2003	High temperature high pressure capsule for processing material in supercritical fluid
RD26623-07	KOREA (SOUTH)	PCT	ABANDONED	10-2005-7014853	KR1020050103290			8/1/2005	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-08	POLAND	PCT	ABANDONED	P.373088				2/12/2003	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-09	SOUTH AFRICA	PCT	LAPSED	2005/06989		2005/06989	12/27/2006	8/31/2005	High temperature high pressure capsule for processing materials in supercritical fluids
RD26623-A	AUSTRALIA	PCT	ABANDONED	2003215191	AU2003216191			2/12/2003	High temperature high pressure capsule for processing materials in supercritical fluids
RD27007-01	TAIWAN	PCT	LAPSED	089120475	89120475 (A)	TW2727122B	2/1/2007	10/2/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-03	WIPO		CLOSED	PCT/US00/26704	WO2001024921			9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride

Serial	Country	Case No.	Status	Applicant Name	Publication Number	Patent Number	Sample	Filing Date	Title
RD27007-36	SINGAPORE	PCT	LAPSED	2002017895		SG88092	4/30/2004	9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-37	UNITED KINGDOM	EPC	LAPSED	00967039.9				9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-12	CANADA	PCT	ABANDONED	CA20002285713	CA2285713			9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-13	MEXICO		ABANDONED	2002/003618				9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27007-A	AUSTRALIA	PCT	LAPSED	AU20003077297D	AU7729700			9/28/2000	Crystalline gallium nitride and method for forming crystalline gallium nitride
RD27904-02	USA	ORD	ABANDONED	09/694990	Non-pub			10/23/2000	Homopitaxial gallium-nitride-based light emitting device and method for producing
RD29614-10	USA	CIP	ABANDONED	11/249672	US2006-0037529 A1			10/19/2005	Single crystal and quasi-single crystal, composition, apparatus, and associated method
RD29614-02	WIPO	PCT	CLOSED	PCT/US08/05114	WO2003083187			2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-04	JAPAN	PCT	ABANDONED	2003-580614	JP2005521625 (A)			2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-06	INDIA	PCT	ABANDONED	2504/DELNP/04				8/26/2004	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-08	POLAND	PCT	ABANDONED	371370	PL371370 (A1)			2/21/2003	High pressure high temperature growth of crystalline group III metal nitrides
RD29614-12	CHINA	DIV	ABANDONED	200710190864.6	CN101230489 A			2/21/2003	Apparatus for producing single crystal and quasi-single crystal, and associated method
5072043-01	USA	PROV	EXPIRED	67/888443				7/28/2010	Apparatus for processing materials at high temperatures and pressures
5072043-02	WIPO	PCT	CLOSED	PCT/US11/045706	WO2012016039A1			7/28/2011	Apparatus for processing materials at high temperatures and pressures
5072043-02	USA	PCT	PENDING	13/812757	US20150122172A1			7/28/2011	Apparatus for processing materials at high temperatures and pressures
5072043-02	JAPAN	PCT	GRANTED	2013821972	JP2013542156A	JP5687344 (B2)	2/19/2016	7/28/2011	Apparatus for processing materials at high temperatures and pressures
5072043-02	RUSSIA	PCT	ABANDONED	2013108775	RU2013108775 (A)			7/28/2011	Apparatus for processing materials at high temperatures and pressures
5072043-02	POLAND	PCT	PENDING	20110402676	PL402676 (A1)			7/28/2011	Apparatus for the treatment of materials at high temperatures and under high pressure